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Dated: March 8, 2007

Signature: 

(Richard J. Botos)

Docket No.: REGIM 3.3-089
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Feltin et al.

Application No.: 10/573,463

Group Art Unit: 2812

Filed: December 1, 2006

Examiner: Not Assigned

For: METHOD OF PRODUCING SELF-
SUPPORTING SUBSTRATES COMPRISING
III-NITRIDES BY MEANS OF
HETEROEPITAXY ON A SACRIFICIAL
LAYER

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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Dear Sir:

It is respectfully requested that the references listed on the enclosed form be made of record and considered with respect to the above-referenced U.S. patent application. A copy of each non-US reference is enclosed. Submission of the present Information Disclosure Statement should not be taken as an admission that the cited references are legally available prior art or that the same are pertinent or material.

In the event that any fee is due in connection with the present Information Disclosure Statement, the Commissioner is hereby authorized to charge the same to our Deposit Account No. 12-1095.

Dated: March 8, 2007

Respectfully submitted,

By: 

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PTO/SB/08A/B (09-06)

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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/573,463-Conf. #9267
				Filing Date	December 1, 2006
				First Named Inventor	Eric Pascal Feltin
				Art Unit	2812
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	REGIM 3.3-089

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	CA	Beaumont B., Vennegues P., Gibart P., "Epitaxial Overgrowth of GaN", Phys. Stat. sol. (b) 227, No. 1, pgs. 1-43, 2001.	
	CB	Lahreche, Vennegues, Beaumont and Gibart, "Growth of high-quality GaN by low pressure metal-organic vapor phase epitaxy (LP-MOVPE) from 3D islands and lateral overgrowth", Journal of Crystal Growth 205, 245 (1999).	
	CC	Mathis et al., "Modeling of threading dislocation reduction in growing GaN layers", Journal of Crystal Growth, 231, pgs 371-390, (2001).	

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